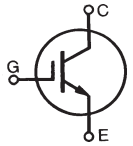
IXYS

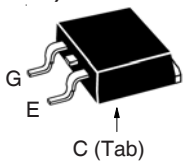
HiPerFAST™ IGBTs
C2-Class
High Speed

IXGA16N60C2
IXGP16N60C2

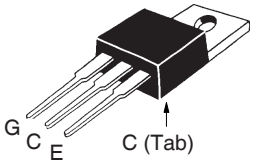
V_{CES} = 600V
I_{C110} = 16A
$V_{CE(sat)}$ ≤ 3.0V
$t_{fi(typ)}$ = 33ns



TO-263 AA (IXGA)



TO-220AB (IXGP)



Symbol	Test Conditions	Maximum Ratings	
V_{CES}	T_J = 25°C to 150°C	600	V
V_{CGR}	T_J = 25°C to 150°C, R_{GE} = 1MΩ	600	V
V_{GES}	Continuous	±20	V
V_{GEM}	Transient	±30	V
I_{C25}	T_C = 25°C	40	A
I_{C110}	T_C = 110°C	16	A
I_{CM}	T_C = 25°C, 1ms	100	A
SSOA (RBSOA)	V_{GE}= 15V, T_J = 125°C, R_G = 22Ω Clamped Inductive load	I_{CM} = 32 $V_{CE} \le V_{CES}$	A
P_C	T_C = 25°C	150	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
M_d	Mounting Torque (TO-220)	1.13/10	Nm/lb.in.
F_C	Mounting Force (TO-263)	10..65 / 2.2..14.6	N/lb.
T_L	Maximum Lead Temperature for Soldering	300	°C
T_{SOLD}	1.6mm (0.062 in.) from Case for 10s	260	°C
Weight	TO-263	2.5	g
	TO-220	3.0	g

G = Gate C = Collector
E = Emitter Tab = Collector

Features

- Optimized for Low Switching Losses
- Square RBSOA
- International Standard Packages

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

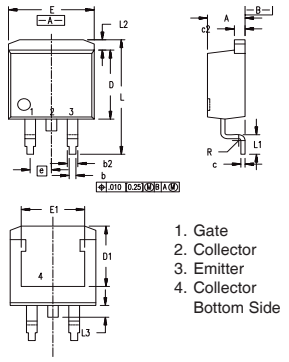
- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{CES}	I_C = 250μA, V_{GE} = 0V	600			V
$V_{GE(th)}$	I_C = 250μA, V_{CE} = V_{GE}	3.0		5.5	V
I_{CES}	V_{CE} = V_{CES}, V_{GE} = 0V			15	μA
	T_J = 125°C			250	μA
I_{GES}	V_{CE} = 0V, V_{GE} = ±20V			±100	nA
$V_{CE(sat)}$	I_C = 12A, V_{GE} = 15V, Note1			3.0	V
	T_J = 125°C		1.8		V

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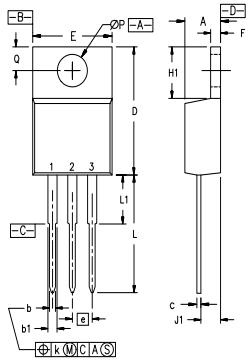
Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	I_C = 12A, V_{CE} = 10V, Note 1	8			S
C_{ies}	V_{CE} = 25V, V_{GE} = 0V, f = 1MHz		657		pF
C_{oes}			62		pF
C_{res}			22		pF
$Q_{g(on)}$	I_C = 12A, V_{GE} = 15V, V_{CE} = 0.5 • V_{CES}		25		nC
Q_{ge}			5		nC
Q_{gc}			13		nC
$t_{d(on)}$	**Inductive load, T_J = 25°C**		16		ns
t_{ri}	I_C = 12A, V_{GE} = 15V		17		ns
E_{on}	V_{CE} = 400V, R_G = 22Ω		0.16		mJ
$t_{d(off)}$	Note 2		75		ns
t_{fi}			33		ns
E_{off}			0.09	0.16	mJ
$t_{d(on)}$	**Inductive load, T_J = 125°C**		16		ns
t_{ri}	I_C = 12A, V_{GE} = 15V		18		ns
E_{on}	V_{CE} = 400V, R_G = 22Ω		0.27		mJ
$t_{d(off)}$	Note 2		115		ns
t_{fi}			100		ns
E_{off}			0.27		mJ
R_{thJC}				0.83	°C/W
R_{thCK}	TO-220		0.50		°C/W

TO-263 (IXGA) Outline



Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.06	4.83	.160	.190
b	0.51	0.99	.020	.039
b2	1.14	1.40	.045	.055
c	0.40	0.74	.016	.029
c2	1.14	1.40	.045	.055
D	8.64	9.65	.340	.380
D1	8.00	8.89	.280	.320
E	9.65	10.41	.380	.405
E1	6.22	8.13	.270	.320
e	2.54	BSC	.100	BSC
L	14.61	15.88	.575	.625
L1	2.29	2.79	.090	.110
L2	1.02	1.40	.040	.055
L3	1.27	1.78	.050	.070
L4	0	0.13	0	.005

TO-220 (IXGP) Outline



Pins: 1 - Gate 2 - Collector
3 - Emitter

SYM	INCHES MIN	MAX	MILLIMETERS MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

Notes:

1. Pulse test, t ≤ 300µs, duty cycle, d ≤ 2%.
2. Switching times & energy losses may increase for higher V_{CE}(Clamp), T_J or R_G.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,850,072 4,881,106 4,931,844 5,017,508 5,034,796 5,049,961 5,063,307 5,187,117 5,237,481 5,381,025 5,486,715 6,162,665 6,259,123 B1 6,306,728 B1 6,404,065 B1 6,534,343 6,583,505 6,683,344 6,710,405 B2 6,710,463 6,727,585 6,759,692 6,771,478 B2 7,005,734 B2 7,063,975 B2 7,071,537 7,157,338B2

Fig. 1. Output Characteristics @ T_J = 25ºC

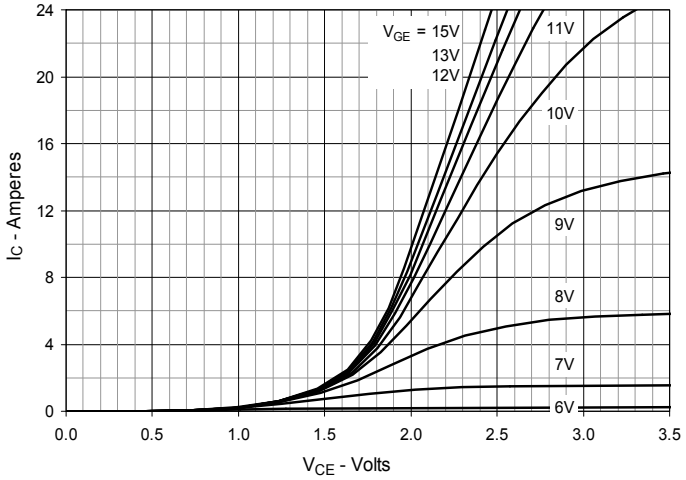


Fig. 2. Extended Output Characteristics @ T_J = 25ºC

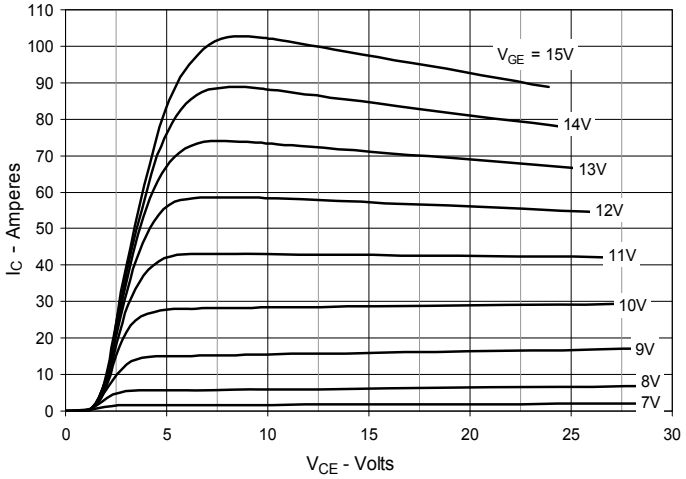


Fig. 3. Output Characteristics @ T_J = 125ºC

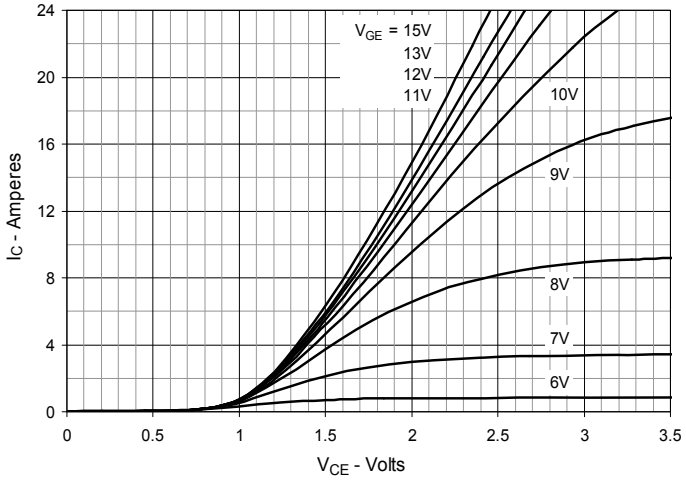


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

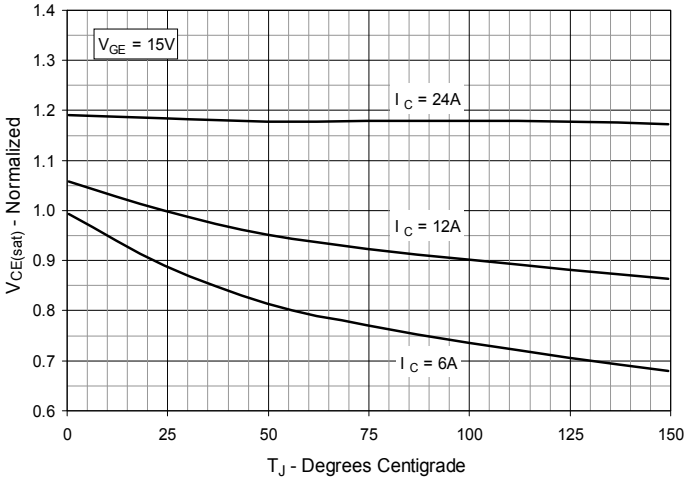


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

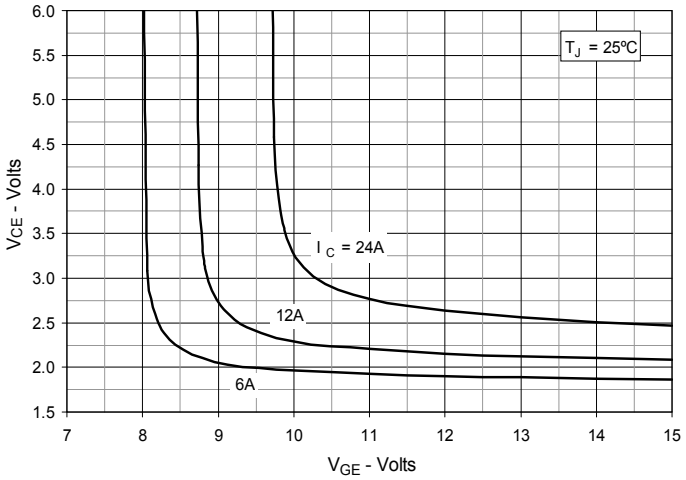
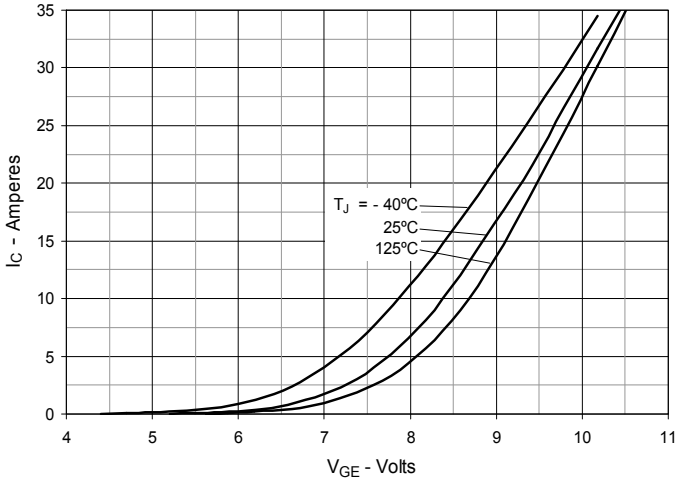


Fig. 6. Input Admittance



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Fig. 7. Transconductance

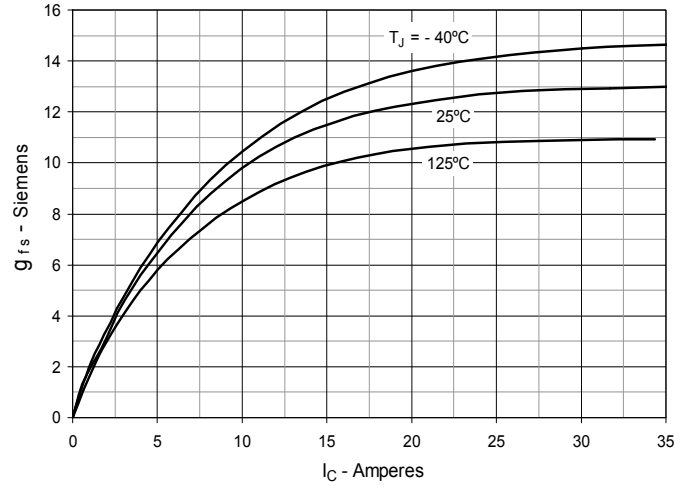


Fig. 8. Gate Charge

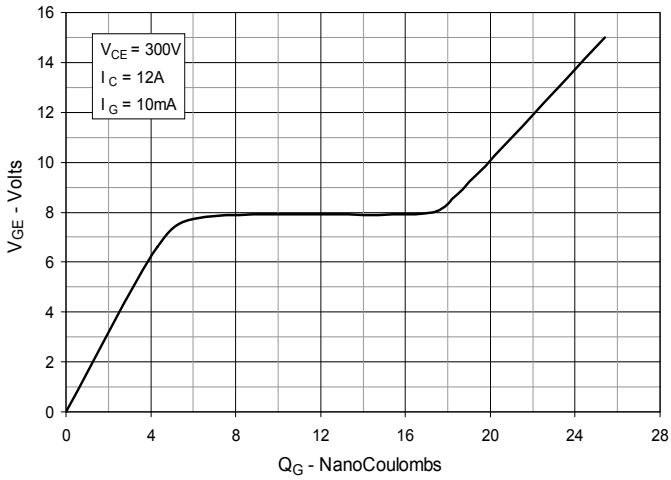


Fig. 9. Capacitance

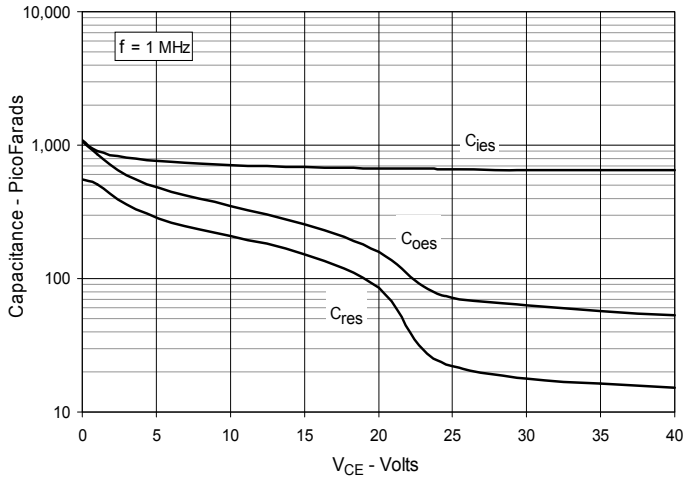


Fig. 10. Reverse-Bias Safe Operating Area

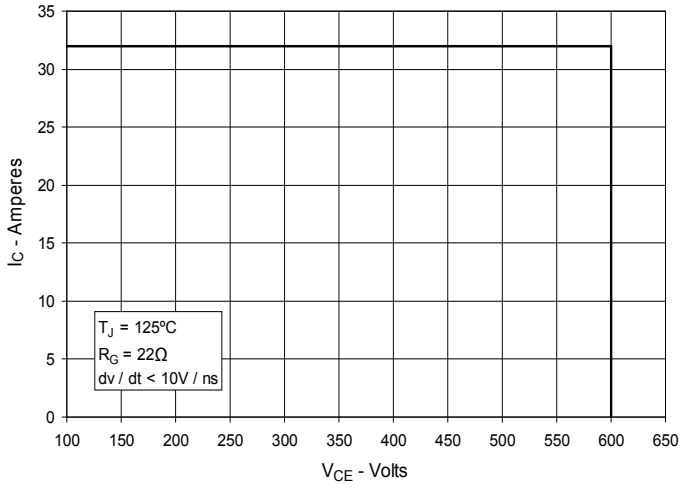
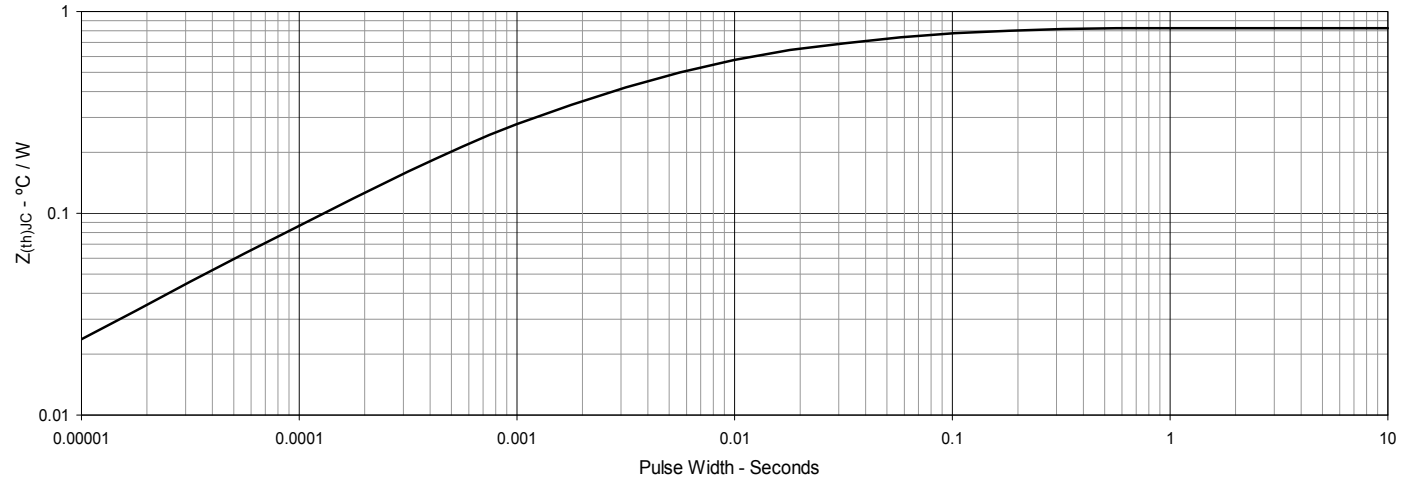


Fig. 11. Maximum Transient Thermal Impedance



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Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance

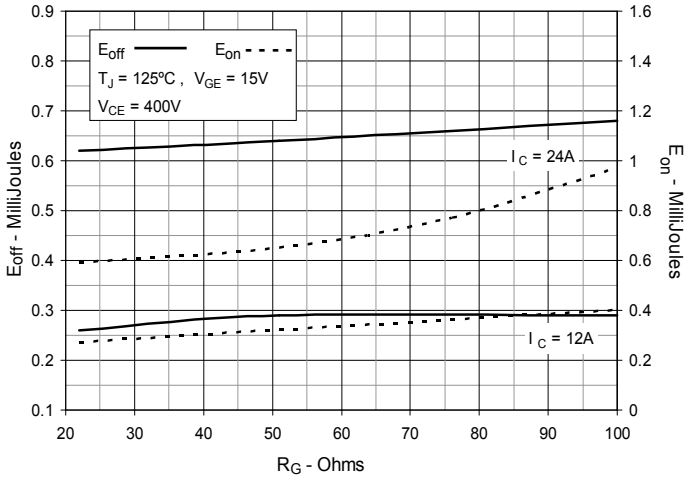


Fig. 13. Inductive Switching Energy Loss vs. Collector Current

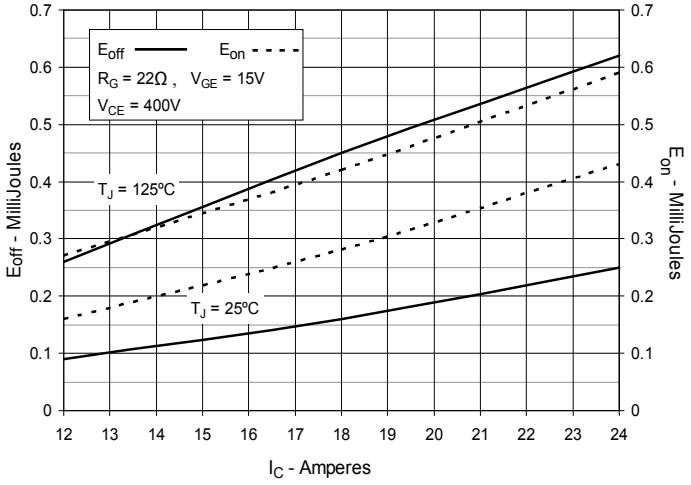


Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature

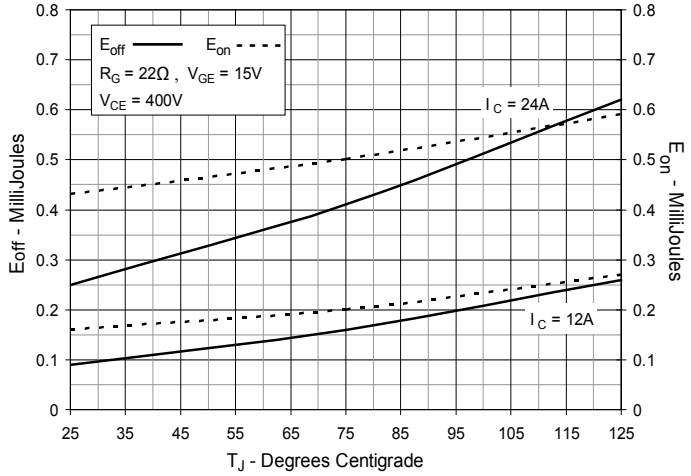


Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance

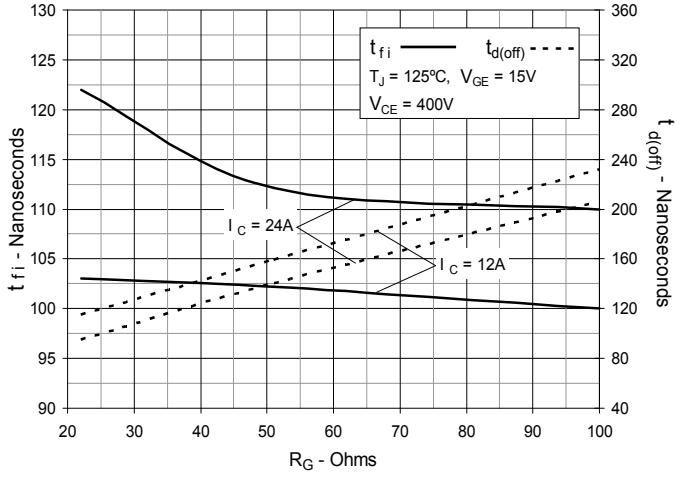


Fig. 16. Inductive Turn-off Switching Times vs. Collector Current

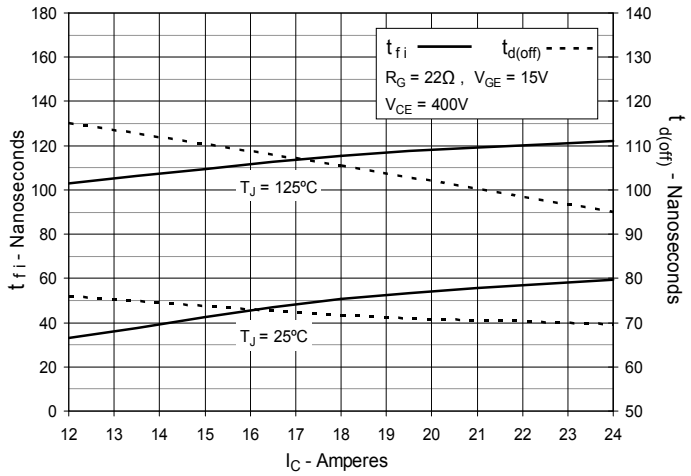
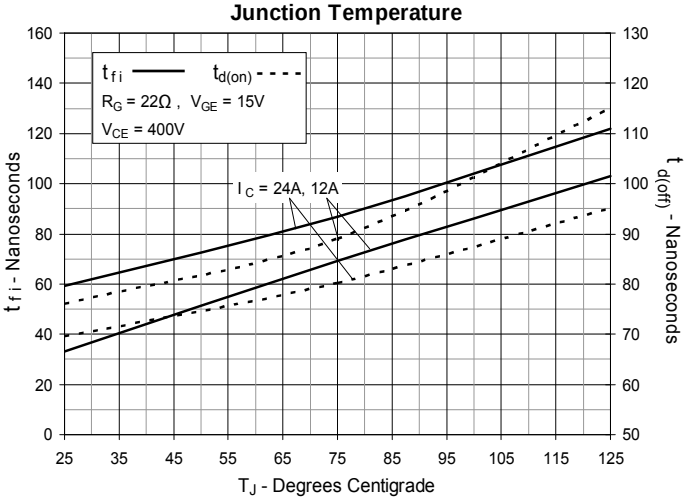


Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature



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Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance

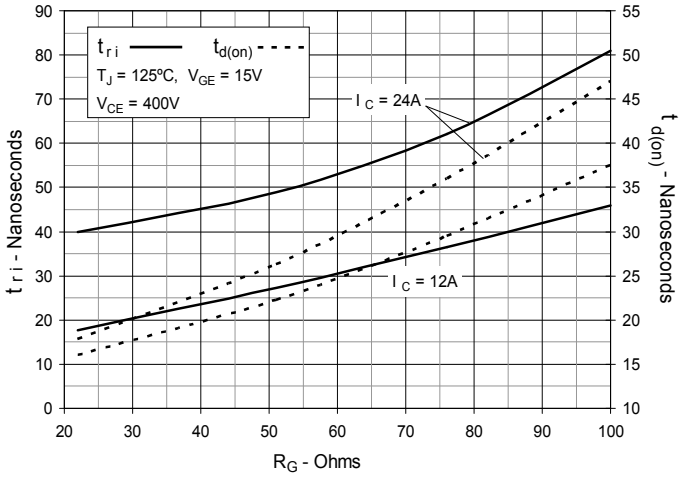


Fig. 19. Inductive Turn-on Switching Times vs. Collector Current

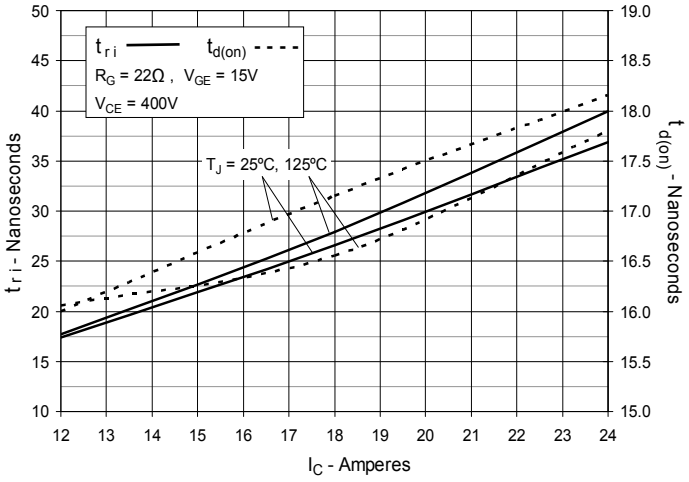


Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature

